

On page 21, please replace the third paragraph with the following:

D2 It is also effective to include fluorine within the atmosphere in forming the thermal oxide film 211. If fluorine is included in the atmosphere in forming the thermal oxide film 211, the nickel element may be fixed and unpaired bonds on the surface of the silicon film may be neutralized. That is, the interfacial characteristics between the active layer and the gate insulating film may be improved.

On page 30, please replace the first paragraph with the following:

D3 Then, contact holes are created to form a source electrode 416 and a drain electrode 417. Finally, a heat treatment of an hour is implemented within a hydrogen atmosphere at 350° C (hydrogen heat treatment). In this step, the defects and unpaired bonds within the active layer are neutralized. Thus, the thin film transistor shown in FIG. 4E is completed.